

NPN Darlington Transistor

This device is designed for applications requiring extremely high gain at collector currents to 1.0 A and high breakdown voltage. Sourced from Process 06.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	100	V
V _{CBO}	Collector-Base Voltage	100	V
V _{EBO}	Emitter-Base Voltage	12	V
Ic	Collector Current - Continuous	1.5	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах			Units
		2N7052	2N7053	*NZT7053	
PD	Total Device Dissipation	625	1,000	1,000	mW
	Derate above 25°C	5.0	8.0	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	125		°C/W
R _{0JA}	Thermal Resistance, Junction to Ambient	200	50	125	°C/W

^{*}Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

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(continued)

Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter Test Conditions		Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	100		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	100		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 1.0 \text{ mA}, I_{\rm C} = 0$	12		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_E = 0$		0.1	μΑ
I _{CES}	Collector-Cutoff Current	$V_{CE} = 80 \text{ V}, I_E = 0$		0.2	μΑ
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 7.0 \text{ V}, I_{C} = 0$		0.1	μΑ

ON CHARACTERISTICS*

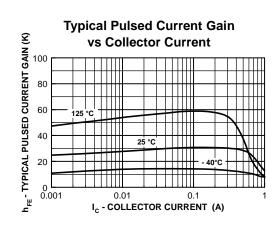
h _{FE}	DC Current Gain	$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}$	10,000 1,000	20,000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 100$ mA, $I_{\rm B} = 0.1$ mA		1.5	V
V _{BE(on)}	Base-Emitter On Voltage	$I_{C} = 100 \text{ mA}, V_{BE} = 5.0 \text{ V}$		2.0	V

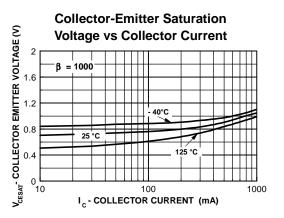
SMALL SIGNAL CHARACTERISTICS

FT	Transition Frequency	$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V},$	200		MHz
C _{cb}	Collector-Base Capacitance	V _{CB} = 10 V,f = 1.0 MHz 2N7052		10	pF
		2N7053		8.0	-

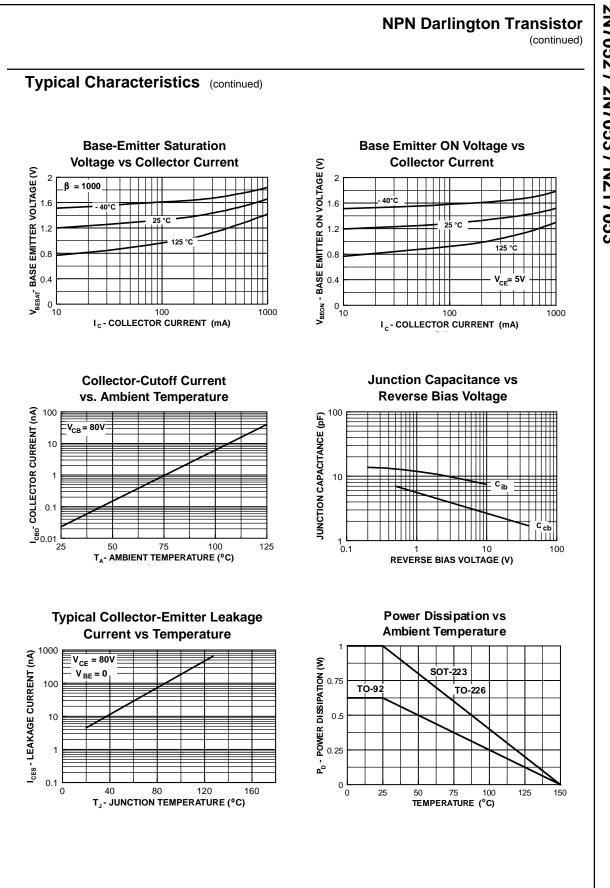
*Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 1.0%

Typical Characteristics





2N7052 / 2N7053 / NZT7053



2N7052 / 2N7053 / NZT7053



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